CVD Synthesis of Single Crystal Diamond Films on Silicon Substrates Without Seeding

Randell Mills*

Jayasree Sankar

Paresh Ray

Bala Dhandapani

Jiliang He

BlackLight Power, Inc.
493 Old Trenton Road
Cranbury, NJ 08512

Single crystal diamond films were synthesized on silicon substrates for the first time without diamond seeding by a microwave plasma reaction of a mixture of 10-30% hydrogen, 90-70% helium, and 1-10% CH_4. The films were characterized by time of flight secondary ion mass spectroscopy (ToF-SIMS), X-ray photoelectron spectroscopy (XPS), Raman spectroscopy, and X-ray diffraction (XRD). It is proposed that He^+ served as a catalyst with atomic hydrogen to form an energetic plasma. The average hydrogen atom temperature was measured to be $180\text{-}210\,eV$ versus $\approx 3\,eV$ for pure hydrogen. The electron temperature T_e for helium-hydrogen was 28,000 K compared to 6800 K for pure helium. Bombardment of the carbon surface by highly energetic hydrogen formed by the catalysis reaction may play a role in the formation of diamond. Then, by this novel pathway, the relevance of the $C-H-O$ tie line is eliminated along with other stringent conditions and complicated and inefficient techniques which limit broad application of the versatility and superiority of diamond thin film technology.

* Phone: 609-490-1090; Fax: 609-490-1066; E-mail: rmills@blacklightpower.com

I. INTRODUCTION

Diamond has some of the most extreme physical properties of any material such as outstanding mechanical strength, optical transparency, high thermal conductivity, high electron mobility, and unique chemical properties [1]. Thus, a variety of possible applications are envisioned for diamond materials. Yet, its practical use in applications has been limited due to its scarcity, expense, and immalleability. The development of techniques for depositing thin films of synthetic diamonds on a variety of substrates has enabled the exploitation of diamond's superlative properties in many new and exciting applications. These include cutting tools, thermal management of integrated circuits, optical windows, high temperature electronics, surface acoustic wave (SAW) filters, field emission displays, electrochemical sensors, composite reinforcement, microchemical devices and sensors, and particle detectors [1]. But, the fundamental impediment facing the technology at the present is insufficient growth rate of high-quality diamond.

Synthetic diamond was initially commercially produced as single crystals using the so-called high-pressure high-temperature (HPHT) growth technique [1] wherein graphite is compressed in a hydraulic press to tens of thousands of atmospheres, heated to over 2000 K, and left until diamond crystallizes. Recent novel HPHT methods which have been largely unsuccessful, except for the production of nanocrystals by Orwa et. al. [2], are based on attempts to use high energy ion implantation to bury carbon deep in metals or fused silica to take advantage of the large confining pressures there. More versatile thin films have been produced by an addition-of-one-atom-at-a-time approach using chemical vapor deposition (CVD) techniques. All CVD techniques for producing diamond films require activation of the gaseous carbon-containing precursor molecules. To promote diamond over graphite growth, the precursor gas is usually CH_4 that is diluted in excess hydrogen that is typically 99% of the reactant mixture, and the temperature of the substrate is usually maintained in excess of 700°C. Activation may be achieved thermally using a hot filament, gas discharge such as DC, RF, or microwave discharges, or a combustion flame such as an oxyacetylene torch [1].

Although the mechanism of diamond growth on a seed of diamond is still somewhat of a mystery, it is believed to be based on the extraction of H of a CH terminal bond to form a dangling carbon center to which CH_3 reacts. A carbon-carbon bond forms between adjacent methyl groups, and the hydrogen is gradually extracted, probably by H forming H_2. The further preferential degradation of graphitic carbon over diamond carbon by hydrogen permits diamond growth [1]. H may also be required to decrease the concentration of gas phase unsaturated hydrocarbons.

More recent advances of diamond formation have been towards developing methods to grow diamond at low temperatures (< 500°C rather than 700°C) such that diamond films can be grown on a wider range of substrate materials of commercial importance with low melting points such as plastics, aluminum, some glasses, nickel, steel and electronics materials such as *GaAs*. Many gas mixtures have been investigated to achieve this goal including ones containing some halogens, presumably substituting for the role played by H [3]. More common mixtures have different combinations of H_2, CH_4, O_2, CO_2, and CO [3]. Quite successful diamond film growth has been achieved at temperatures as low as 180°C using gas mixtures of CH_4 mixed with CO_2 or CO in microwave plasma deposition reactors wherein an optimal rate is obtained when the gas ratio is about 50/50%. Although the concentration of H_2 in the activated gas mixture is approximately half that seen in the CH_4/ H_2 mixtures [4], the CO_2-CH_4 and CO-CH_4 systems are unique in that hydrogen is low compared to the excess needed in other systems presumably because oxygen species such as O_2, O, and OH in the CO_2-CH_4 and CO-CH_4-system plasmas perform the same role as H in the CH_4-H_2-system plasmas. Recent molecular beam mass spectroscopy investigations of the CO_2-CH_4 system indicate the incorporation of CH_3 at a dangling carbon bond is the most probable mechanism as in the case of the CH_4-H_2 system. However, the species that extracts H may not be an oxygen species. Rather, CO may activate the surface by extracting a terminating H [5].

Empirically it is known that only narrow set of ratios of O, C, and H result in diamond formation. Using the combined data from over 70 diamond deposition experiments, Bachmann et al. produced a $C-H-O$

phase diagram for diamond deposition which showed that low pressure diamond synthesis is only possible within a very narrow well-defined domain centered on a line called the $C-H-O$ tie line [6-7]. A consequence of this analysis was that the exact nature of the plasma gases was unimportant for most CVD processes; rather, the relative ratios of O, C, and H controlled the deposition.

It was previously reported that a novel highly stable surface coating SiH which comprised high binding energy hydride ions was synthesized by microwave plasma reaction of mixture of silane, hydrogen, and helium wherein it was proposed that He^+ served as a catalyst with atomic hydrogen to form the highly stable hydride ions [8]. The novel silicon hydride was identified by time of flight secondary ion mass spectroscopy (ToF-SIMS) and X-ray photoelectron spectroscopy (XPS). ToF-SIMS identified the coatings as hydride by the large SiH^+ peak in the positive spectrum and the dominant H^- in the negative spectrum. XPS identified the H content of the SiH coatings as hydride ions corresponding to peaks at 11, 43, and 55 eV with no corresponding primary element peaks. The silicon hydride surface was remarkably stable in air for long duration exposure as shown by XPS.

In the quest for low temperature diamond synthesis, CH_4 was substituted for SiH_4 in the helium-hydrogen microwave reaction which formed novel SiH. We report for the first time the deposition of single crystal diamond films on silicon-wafers by a helium-hydrogen-CH_4 (90-70/10-30/1-10%) microwave plasma maintained with an Evenson cavity without diamond seeding or abrasion that provides seed crystals [9]. After the plasma processing reaction, the surface was characterized by ToF-SIMS, XPS, Raman spectroscopy, and X-ray diffraction (XRD). In order to understand the role of the helium-hydrogen plasma, it was characterized by recording the line broadening of the 656.3 nm Balmer α line to determine the excited hydrogen atom energy. The electron temperature T_e was also measured using the ratio of the intensity I of two lines in two quantum states such as the ratio $I(He\ 501.6\ nm\ line)/\ I(He\ 492.2\ nm\ line)$.

II. EXPERIMENTAL

Synthesis

Diamond films were grown on silicon wafer substrates by their exposure to a low pressure $He/ H_2/ CH_4$ microwave plasma. The experimental set up comprising a microwave discharge cell operated under flow conditions is shown in Figure 1. A silicon wafer substrate (0.5 X 0.5 X 0.05 cm, Silicon Quest International, silicon (100), boron doped) cleaned by heating to 700°C under vacuum was placed about 2 cm off center inside of a quartz tube (1.2 cm in diameter by 25 cm long) with vacuum valves at both ends. The tube was center-fitted with an Opthos coaxial microwave cavity (Evenson cavity) and connected to the gas/vacuum line. The quartz tube and vacuum line were evacuated for 2 hours to remove any trace moisture or oxygen and residual gases. A premixed He (90-70%)/H_2 (10-30%)/CH_4 (1-10%) plasma gas was flowed through the quartz tube at a total pressure of 1.5 Torr maintained with a gas flow rate of 40 sccm controlled by a mass flow controller with a readout. The cell pressure was monitored by an absolute pressure gauge. The microwave generator shown in Figure 1 was an Opthos model MPG-4M generator (Frequency: 2450 MHz). The microwave plasma was maintained with a 40 W (forward)/2 W (reflected) power for about 12-16 hrs. The substrate was at the cool edge of the plasma glow region. The wall temperature at this position was about 300°C. A thick (~100 μm) crystalline, shiny coating formed on the substrate and the wall of the quartz reactor. The quartz tube was removed and transferred to a drybox with the samples inside by closing the vacuum valves at both ends and detaching the tube from the vacuum/gas line. The coated silicon wafer substrate was mounted on XPS and ToF-SIMS sample holders under an argon atmosphere in order to prepare samples for the corresponding analyses. Controls for XPS analysis comprised a cleaned commercial silicon wafer (Silicon Quest International, silicon (100), boron doped) and known standards: (a) single crystal diamond, (b) diamond film, (c) glassy carbon, (d) pyrolytic graphite, (e) mineral graphite, and (f) HDLC (hydrogenated diamond-like carbon). The control for ToF-SIMS analysis comprised a cleaned commercial silicon wafer (Silicon Quest International, silicon (100), boron doped). The coated substrate was also sent for Raman analysis (Charles Evans & Associates, Sunnyvale, CA) and XRD analysis (IC Laboratories, Amawalk, NY).

ToF-SIMS Characterization

A cleaned commercial silicon wafer before and after plasma treatment to form a diamond film coating were characterized using a Physical Electronics TRIFT ToF-SIMS instrument. The primary ion source was a pulsed $^{69}Ga^{+}$ liquid metal source operated at 15 keV. The secondary ions were exacted by a ± 3 keV (according to the mode) voltage. Three electrostatic analyzers (Triple-Focusing-Time-of-Flight) deflect them in order to compensate for the initial energy dispersion of ions of the same mass. The 400 pA dc current was pulsed at a 5 kHz repetition rate with a 7 ns pulse width. The analyzed area was $60\mu m$ x $60\mu m$ and the mass range was 0-1000 AMU. The total ion dose was $7X10^{11}\ ions/cm^2$, ensuring static conditions. Charge compensation was performed with a pulsed electron gun operated at 20 eV electron energy. In order to remove surface contaminants and expose a fresh surface for analysis, the samples were sputter-cleaned for 30 s using a $80\mu m$ x $80\mu m$ raster, with 600 pA current, resulting in a total ion dose of $10^{15}\ ions/cm^2$. Three different regions on each sample of $60\mu m$ x $60\mu m$ were analyzed. The positive and negative SIMS spectra were acquired. Representative post sputtering data is reported. The ToF-SIMS data were treated using 'Cadence' software (Physical Electronics), which calculates the mass calibration from well-defined reference peaks.

XPS Characterization

A series of XPS analyses were made on the samples using a Scienta 300 XPS Spectrometer at Lehigh University, Bethlehem, PA. The fixed analyzer transmission mode and the sweep acquisition mode were used. The Aluminum X-ray incidence angle was 15°. The step energy in the survey scan was $0.5\,eV$, and the step energy in the high resolution scan was $0.15\,eV$. In the survey scan, the time per step was 0.4 seconds, and the number of sweeps was 4. In the high resolution scan, the time per step was 0.3 seconds, and the number of sweeps was 30. $C\,1s$ at $284.6\,eV$ was used as the internal standard.

Raman Spectroscopy

Experimental and control samples were analyzed by Charles Evans & Associates, Sunnyvale, CA. Raman spectra were obtained with a LABRAM spectrometer (Dilor of Jobin Yvon) with a Spectrum One CCD (charge coupled device) detector (Spex and Jobin Yvon) that was air and Peltier cooled. An Omnichrome HeNe laser (Melles Griot) with the light wavelength of 632.817 nm was used as the excitation source. The spectra were taken at ambient conditions and the samples were placed under a Raman microscope (Olympus BX40). Spectra of the film samples were acquired using the following condition: the laser power at the sample was 4 to 8 mW, the slit width of the monochromator was 100 μm which corresponds to a resolution of 3 cm^{-1}, the detector exposure time was 20 mins., and 3 scans were averaged.

Characterization by X-ray Diffraction (XRD)

The XRD patterns were obtained by IC Laboratories (Amawalk, NY) using a Phillips 547 Diffractometer tuned for $Cu\,K_\alpha$ (1.540590 Å) radiation generated at 45 kV and 35 mA. The sample was scanned from 10 to 100 2-theta (2θ) with a step size of 0.02° and 1 second per step.

Balmer α line broadening and T_e measurements

The width of the 656.3 nm Balmer α line emitted from hydrogen alone, xenon-hydrogen mixture (90/10)%, and helium-hydrogen mixture (90/10)% microwave discharge plasmas maintained in the microwave discharge cell shown in Figure 1 was measured with a high resolution visible spectrometer capable of a resolution of $\pm 0.006\,nm$ [10-11]. In this case, the total pressure was 1 Torr, and the input power to the plasma was set at 40 W.

T_e was measured on 0.1 Torr microwave plasmas of helium or hydrogen alone, xenon-hydrogen mixture (90/10%), and helium-hydrogen mixture (90/10%) using the ratio of the intensity I of two lines in two quantum states. For example, T_e was measured on helium from the ratio of the intensity of the *He* 501.6 nm (upper quantum level n=3) line to that of the *He* 492.2 nm (n=4) line as described by Griem [12], and T_e was measured on hydrogen alone plasmas from their Balmer line intensities. The visible spectrum $400-560\,nm$ was recorded with a normal

incidence EUV spectrometer using a PMT and a sodium salicylate scintillator as described previously [10-11].

. The electron density was determined using a Langmuir probe according to the method given previously [13].

III. RESULTS

ToF-SIMS

The positive ion ToF-SIMS spectra of a cleaned commercial silicon wafer before and after being coated with a carbon film are shown in Figures 2 and 3, respectively. The positive ion spectrum of the control was dominated by Si^+, oxides $Si_xO_y^+$, and hydroxides $Si_x(OH)_y^+$; whereas, that of the carbon film sample contained no silicon containing fragments. Rather, a large H^+ peak and trace hydrocarbon fragments $C_xH_y^+$ were observed. The $m/e = 69$ peak was due to the Ga^+.

The negative ion ToF-SIMS spectra of a cleaned commercial silicon wafer before and after being coated with a carbon film are shown in Figures 4 and 5, respectively. The control spectrum was dominated by oxide (O^-) and hydroxide (OH^-); whereas, spectrum of the carbon film was dominated by hydride ion (H^-) and carbon ion (C^-). Very little oxide (O^-) or hydroxide (OH^-) was observed. An exceptional feature was the multimeric carbon clusters C_x^- at $m/e = 12, 24, 36, 48, 60, 72, 96, 108, 120$.

XPS

A survey spectrum was obtained over the region $E_b = 0\ eV$ to $1200\ eV$. The primary element peaks allowed for the determination of all of the elements present. The XPS survey scan of a cleaned commercial silicon wafer before and after being coated with a carbon film are shown in Figures 6 and 7, respectively. The major peaks identified in the XPS spectrum of the control sample were $O\,1s$ at 533.0 eV, trace $C\,1s$ at 284.6 eV, dominant $Si\,2s$ at 152.4 eV and $Si\,2p_{3/2}$ at 101.9 eV. Whereas, the carbon film sample comprised only carbon and trace silicon and oxygen contamination as indicated by the trace $O\,1s$ peak at 532.9 eV, the trace $Si\,2s$ at 153.2 eV and $Si\,2p_{3/2}$ at 102.2 eV, and the dominant $C\,1s$ peak at 284.6 eV.

The high resolution XPS spectra (0-35 eV) of the valence band region of (a) single crystal diamond, (b) diamond film, (c) glassy carbon, (d) pyrolytic graphite, (e) mineral graphite, and (f) HDLC are shown in Figure 8 [14]. The corresponding XPS spectrum of the carbon film sample is shown in Figure 9. The film had a sharp peak at 13.2 eV and a broad peak at 17.4 eV which matched the peak energies of single crystal diamond rather than that of the other forms of carbon which were observed at higher binding energies. No $O\,2s$ peak was also observed in the region of 23 eV as shown in Figure 9.

The high resolution XPS spectra (280-340 eV) of the $C\,1s$ energy loss region of (a) single crystal diamond, (b) diamond film, (c) glassy carbon, (d) pyrolytic graphite, (e) mineral graphite, and (f) HDLC are shown in Figure 10 [14]. The corresponding XPS spectrum of the carbon film sample is shown in Figure 11. Single crystal diamond, diamond film, and HDLC have an energy loss feature which begins at about 290 eV which is at a higher energy than that of the other possible forms of carbon as shown in Figure 10. The closest match to the shape of the energy loss feature of the carbon film is single crystal diamond to which the film was assigned.

Raman

The Raman spectrum of the corresponding region of the diamond film is shown in Figure 12. The peak positions, full-width-half-maximum (FWHM), and peak areas were calculated by Gaussian curve fitting the baseline corrected spectrum. The diamond band was observed at 1323.5 cm^{-1}, with a FWHM of 19.6 cm^{-1}. The diamond peak width of less that 20 cm^{-1} identified the film as having single crystal diamond [15]. In addition to the diamond band, the D-band, G-band of diamond-like carbon (DLC), and G-band of graphite were observed at 1327.0 cm^{-1} with a FWHM of 76 cm^{-1}, 1484.0 cm^{-1} with a FWHM of 130.2 cm^{-1}, and 1591.6 cm^{-1} with a FWHM of 46.5 cm^{-1}, respectively.

The ratio of the areas of the diamond peak to G-band of graphite, $\frac{I_D}{I_G}$, is considered an indirect measure of carbon $\frac{sp^3}{sp^2}$ bonding ratio. The ratio $\frac{I_D}{I_G}$ was 0.73. The Raman spectrum confirmed the XPS results that

the film comprised diamond. Based on quantitative studies [16-17], we estimate that the diamond composition of the films was well over 50%.

XRD

The X-ray Diffraction (XRD) pattern of the diamond film for 2θ = 10° to 100° is shown in Figure 13. The dominant peaks were due to silicon of the substrate. Diamond peaks were observed at 2θ = 43.9° (111) and 75.3° (220) [18-19]. Additional peaks other than silicon and diamond corresponded to DLC.

Line broadening and T_e measurements

The Doppler-broadened line shape for atomic hydrogen has been studied on many sources such as hollow cathode [20-21] and rf [22-23] discharges. The method of Videnovic et al. [20] was used to calculate the energetic hydrogen atom densities and energies from the width of the 656.3 nm Balmer α line emitted from microwave discharge plasmas of hydrogen compared with each of xenon-hydrogen (90/10%) and helium-hydrogen (90/10%) as shown in Figures 14-15, respectively. Gigosos et al. [24] have published a literature review of this method. The average helium-hydrogen Doppler half-width of $0.52 \pm 5\% nm$ was not appreciably changed with pressure. The corresponding energy of $180\text{-}210\, eV$ and the number densities of $5 X 10^{14} \pm 20\% atoms/cm^3$, depending on the pressure, were significant compared to only $\approx 3\, eV$ and $7 X 10^{13} \pm 20\% atoms/cm^3$ for pure hydrogen, even though 10 times more hydrogen was present. Xenon did not serve as a catalyst, and the plasma was much less energetic. Xenon-hydrogen showed no excessive broadening corresponding to an average hydrogen atom temperature of $\approx 3\, eV$, and the atom density was also low, $3 X 10^{13} \pm 20\% atoms/cm^3$.

Similarly, the average electron temperature for helium-hydrogen plasma was $28{,}000 \pm 5\% K$. Whereas, the corresponding temperature of helium alone was only $6800 \pm 5\% K$, hydrogen alone was $5500 \pm 5\% K$, and xenon-hydrogen was $6500 \pm 5\% K$.

We have assumed that Doppler broadening due to thermal motion was the dominant source to the extent that other sources may be neglected. This assumption was confirmed when each source was considered. In general, the experimental profile is a convolution of two

Doppler profiles, an instrumental profile, the natural (lifetime) profile, Stark profiles, Van der Waals profiles, a resonance profile, and fine structure. The electron density recorded with a Langmuir probe was five orders of magnitude too low for detectable Stark broadening, and the contribution from each remaining source was determined to be below the limit of detection [10-11].

IV. DISCUSSION

Silicon substrates were coated by the reaction product of a low pressure *He* (90-70%)/H_2 (10-30%)/CH_4 (1-10%) microwave discharge plasma. The ToF-SIMS of the carbon film showed carbon clusters, and the XPS matched single crystal diamond which was confirmed by the Raman diamond peak at 1323.5 cm^{-1} with a FWHM of less than 20 cm^{-1}. Diamond is proposed to form from CH_4 by the catalytic reaction of He^+ with atomic hydrogen which forms an energetic plasma which was measured to have extraordinarily fast H.

In the previously developed CH_4-H_2-system and variations thereof, diamond formation occurs within a small domain about the $C-H-O$ tie line. Stringent conditions of a large excess of hydrogen, diamond seeding, and an elevated temperature are required. Similarly, in the CO_2/ CH_4 system, diamond only formed within a range of a few percent from a 50/50% mixture. We observed for the first time that diamond was very reproducibly formed from a CH_4 carbon source with a helium-hydrogen plasma without the requirements of diamond seeding, an elevated temperature, or an excess of hydrogen, or any particular former set of stringent conditions. Thus, a dramatic breakthrough in thin film diamond deposition has been shown.

The mechanism may be based on energetic hydrogen formed in the plasma reaction. Diamond and DLC are metastable materials; thus, continuous bombardment of the surface with energetic species that produce thermal and pressure spikes at the growth surface is required for deposition of diamond, DLC, and related films [25]. By quenching a beam of C^+ ions accelerated in an ultrahigh vacuum to a negatively biased substrate, Aisenberg and Chabot [26] were able to deposit DLC films for the first time. Rather than resulting in commercially useful

processes, subsequently developed beam-type and sputtering production methods are essentially used for research. Exemplary methods discussed by Grill and Myerson [27] are single low-energy beams of carbon ions, dual ion beams of carbon and argon, ion plating, RF sputtering or ion-beam sputtering from carbon/graphite targets, vacuum-arc discharges, and laser ablation. Using sputter deposition, amorphous DLC coatings can be prepared at low temperature due to high ion bombardment during the deposition of carbon. The absence of ion bombardment during carbon deposition leads to soft, conductive carbon films with no diamond-like properties. It has been shown that films with diamond-like properties are produced at ion energies of about 100 eV [28-29].

Energetic species such as fast H formed in the helium-hydrogen microwave plasma that showed extraordinary Balmer α line broadening corresponding to an average hydrogen atom temperature of $180\text{-}210\,eV$ may be the basis of the formation of the diamond film from CH_4. Without diamond seeding, production of single crystal diamond films on heterogeneous substrates was achieved under relatively low temperature, nonstringent conditions.

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Figure Captions

Figure 1. The experimental set up comprising a microwave discharge cell operated under flow conditions.

Figure 2. The positive ion ToF-SIMS spectra ($m/e = 0-800$) of a noncoated cleaned commercial silicon wafer.

Figure 3. The positive ion ToF-SIMS spectra ($m/e = 0-200$) of a cleaned commercial silicon wafer coated by reaction of a helium-hydrogen plasma with CH_4 as the source of C that showed a large H^+ peak and trace hydrocarbon fragments $C_xH_y^+$.

Figure 4. The negative ion ToF-SIMS spectrum ($m/e = 0-800$) of a noncoated cleaned commercial silicon wafer.

Figure 5. The negative ion ToF-SIMS spectrum ($m/e = 0-200$) of a cleaned commercial silicon wafer coated by reaction of a helium-hydrogen plasma with CH_4 as the source of C that was dominated by hydride ion (H^-) and carbon ion (C^-). Very little oxide (O^-) or hydroxide (OH^-) was observed. An exceptional feature was the multimeric carbon clusters C_x^- at $m/e = 12,24,36,48,60,72,96,108,120$.

Figure 6. The XPS survey scan of a cleaned commercial silicon wafer. Only silicon, oxygen, and trace carbon contamination were observed.

Figure 7. The XPS survey scan of a cleaned commercial silicon wafer coated by reaction of a helium-hydrogen plasma with CH_4 as the source of C. Only carbon and trace silicon and oxygen contamination were observed.

Figure 8. High resolution XPS spectra (0-35 eV) of the valence band region of (a) single crystal diamond, (b) diamond film, (c) glassy carbon, (d) pyrolytic graphite, (e) mineral graphite, and (f) HDLC.

Figure 9. High resolution XPS spectra (0-35 eV) of the valence band region of a cleaned commercial silicon wafer coated by reaction of a helium-hydrogen plasma with CH_4 as the source of C that showed features that matched single crystal diamond.

Figure 10. High resolution XPS spectra (280-340 eV) of the $C\,1s$ energy loss region of (a) single crystal diamond, (b) diamond film, (c) glassy carbon, (d) pyrolytic graphite, (e) mineral graphite, and (f) HDLC.

Figure 11. High resolution XPS spectrum (280-340 eV) of the $C\,1s$ energy loss region of a cleaned commercial silicon wafer coated by reaction of a helium-hydrogen plasma with CH_4 as the source of C that showed features that matched single crystal diamond.

Figure 12. The Raman spectrum recorded on the diamond film. The diamond band, D-band, G-band of DLC, and G-band of graphite were observed at 1323.5 cm^{-1}, 1327.0 cm^{-1}, 1484.0 cm^{-1} and 1591.6 cm^{-1}, respectively. The 19.6 cm^{-1} FWHM of the diamond peak is characteristic of and identified the film as having single crystal diamond.

Figure 13. The X-ray Diffraction (XRD) pattern of a diamond film for 2θ = 10° to 100°. The dominant peaks were due to silicon of the substrate. Diamond peaks were observed at 2θ = 43.9° (111) and 75.3° (220).

Figure 14. The 656.3 nm Balmer α line width recorded with a high resolution ($\pm 0.006\,nm$) visible spectrometer on a xenon-hydrogen (90/10%) and a hydrogen microwave discharge plasma. No line excessive broadening was observed corresponding to an average hydrogen atom temperature of $3-4\,eV$.

Figure 15. The 656.3 nm Balmer α line width recorded with a high resolution ($\pm 0.006\,nm$) visible spectrometer on a helium-hydrogen (90/10%) and a hydrogen microwave discharge plasma. Significant broadening was observed corresponding to an average hydrogen atom temperature of $180-210\,eV$.

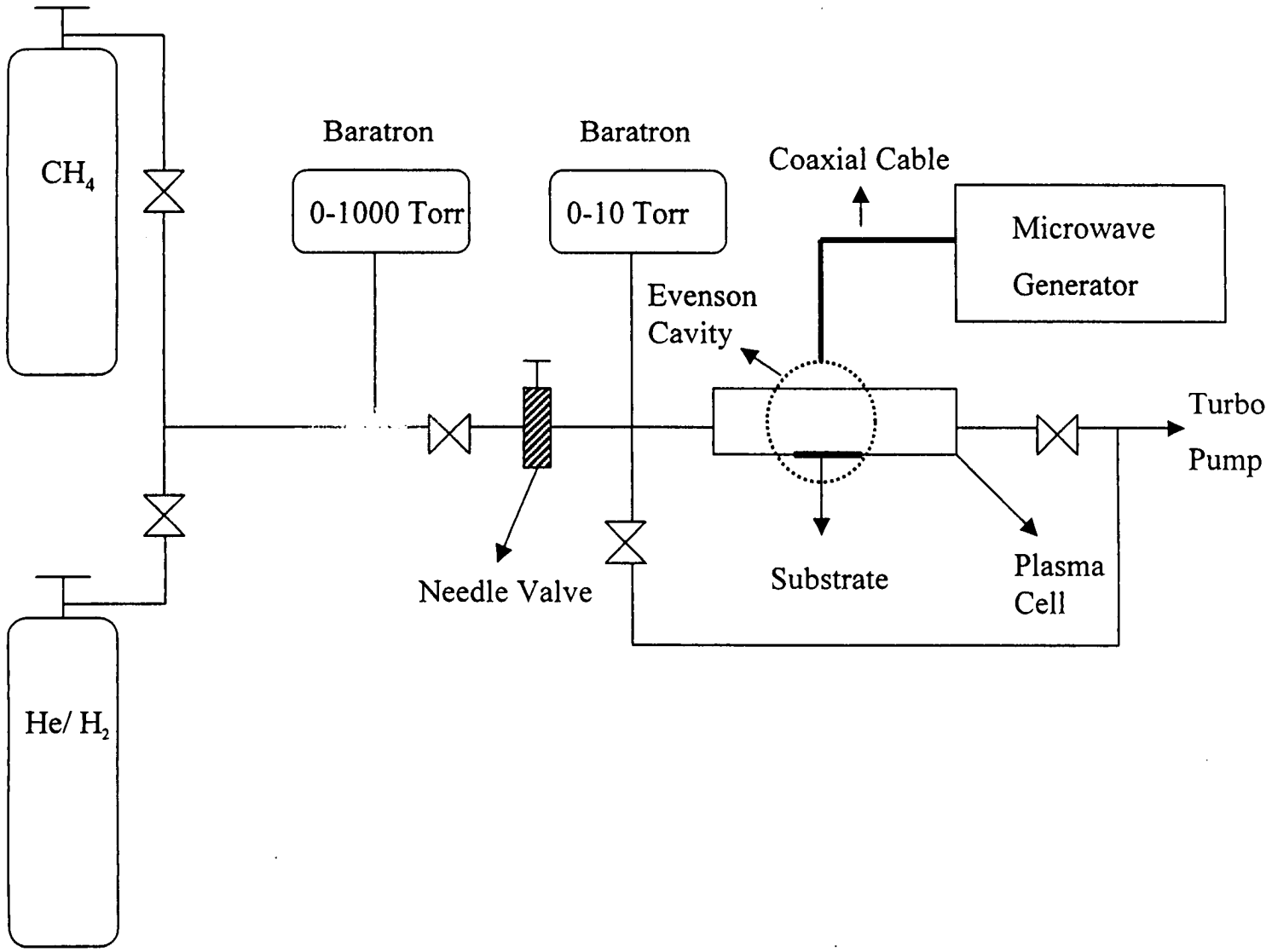
CH_4
Baratron
0-1000 Torr
Baratron
0-10 Torr
Coaxial Cable
Microwave
Generator
Evenson
Cavity
Turbo
Pump
Needle Valve
Substrate
Plasma
Cell
He/ H_2

Fig. 1

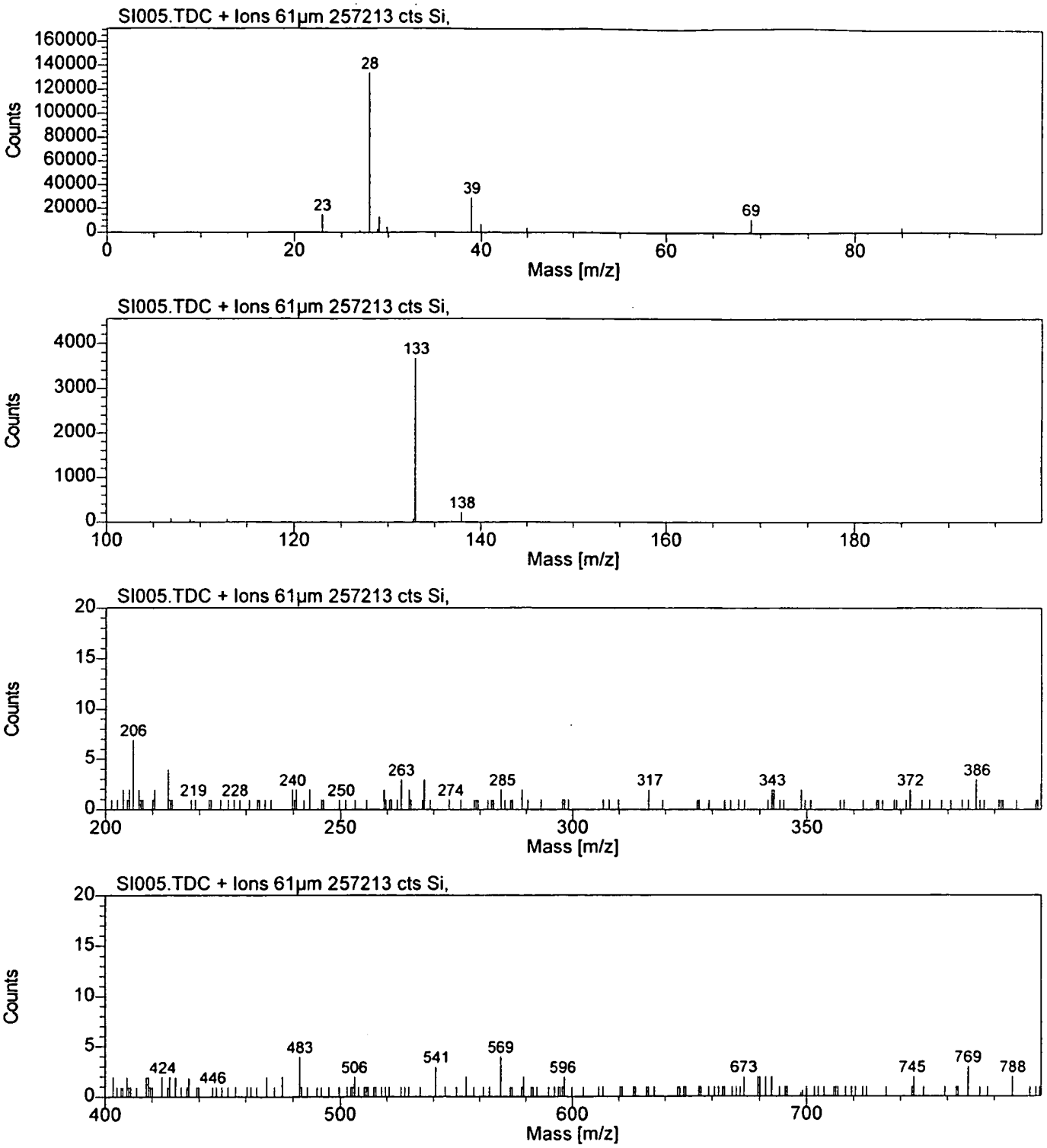
SI005.TDC + Ions 61µm 257213 cts Si,
Counts
Mass [m/z]
28
23
39
69
SI005.TDC + Ions 61µm 257213 cts Si,
133
138
SI005.TDC + Ions 61µm 257213 cts Si,
206
219
228
240
250
263
274
285
317
343
372
386
SI005.TDC + Ions 61µm 257213 cts Si,
424
446
483
506
541
569
596
673
745
769
788

Fig. 2

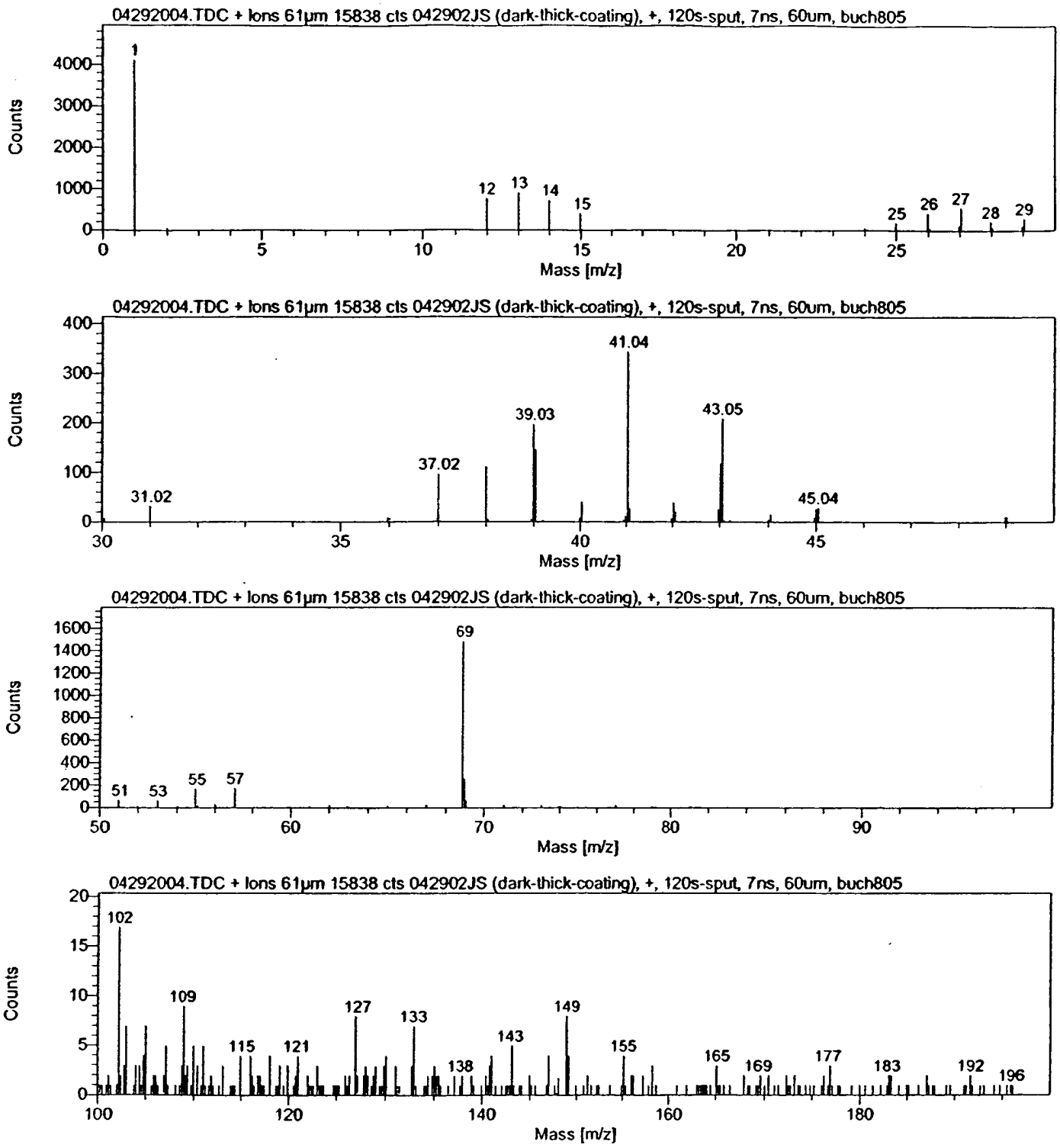
04292004.TDC + Ions 61µm 15838 cts 042902JS (dark-thick-coating), +, 120s-sput, 7ns, 60um, buch805
Counts
Mass [m/z]
1
12
13
14
15
25
26
27
28
29
41.04
39.03
43.05
37.02
31.02
45.04
69
51
53
55
57
102
109
127
133
149
115
121
143
155
138
165
169
177
183
192
196

Fig. 3

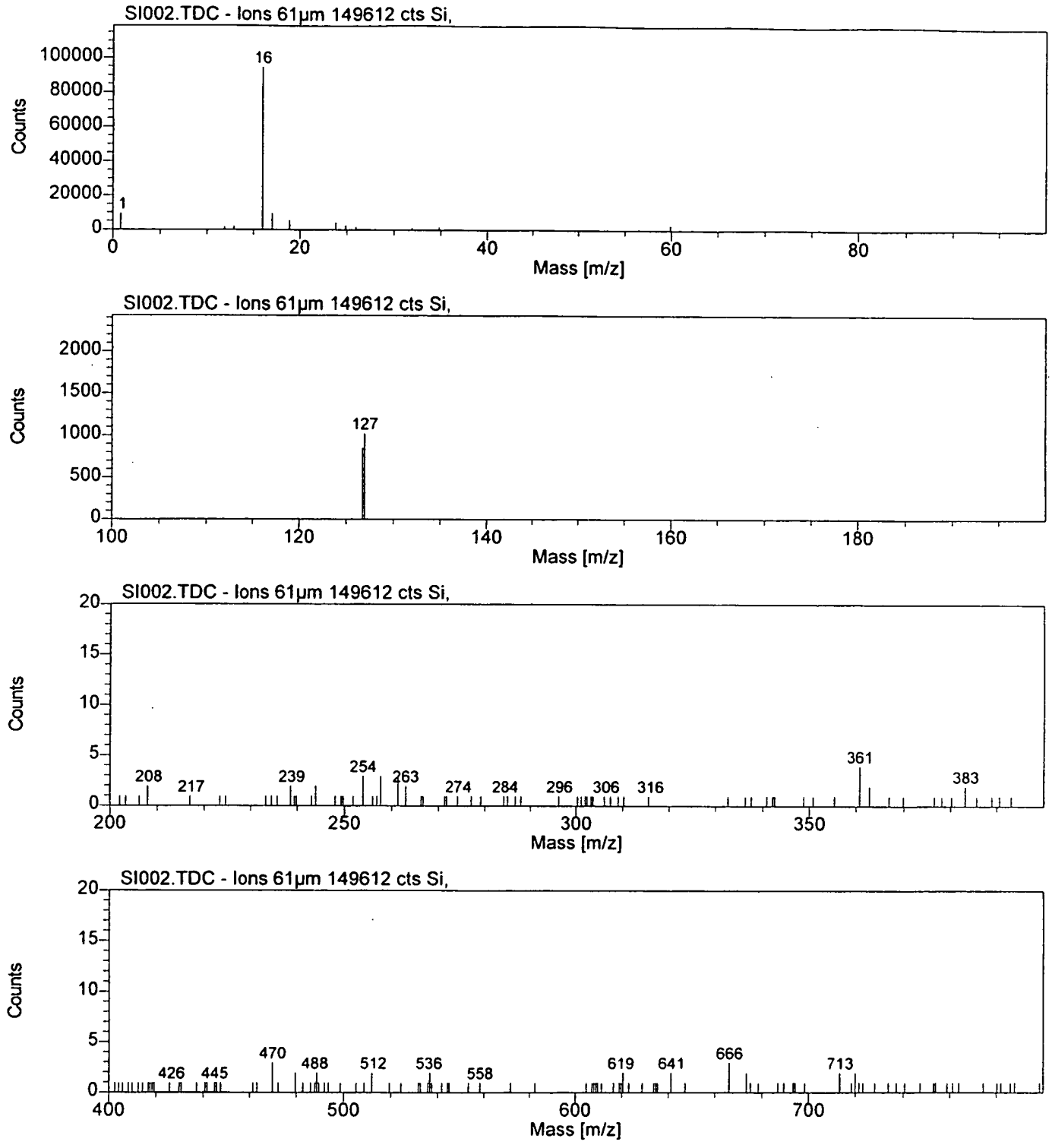
SI002.TDC - Ions 61µm 149612 cts Si,
Counts
Mass [m/z]
16
1
127
208
217
239
254
263
274
284
296
306
316
361
383
426
445
470
488
512
536
558
619
641
666
713

Fig. 4

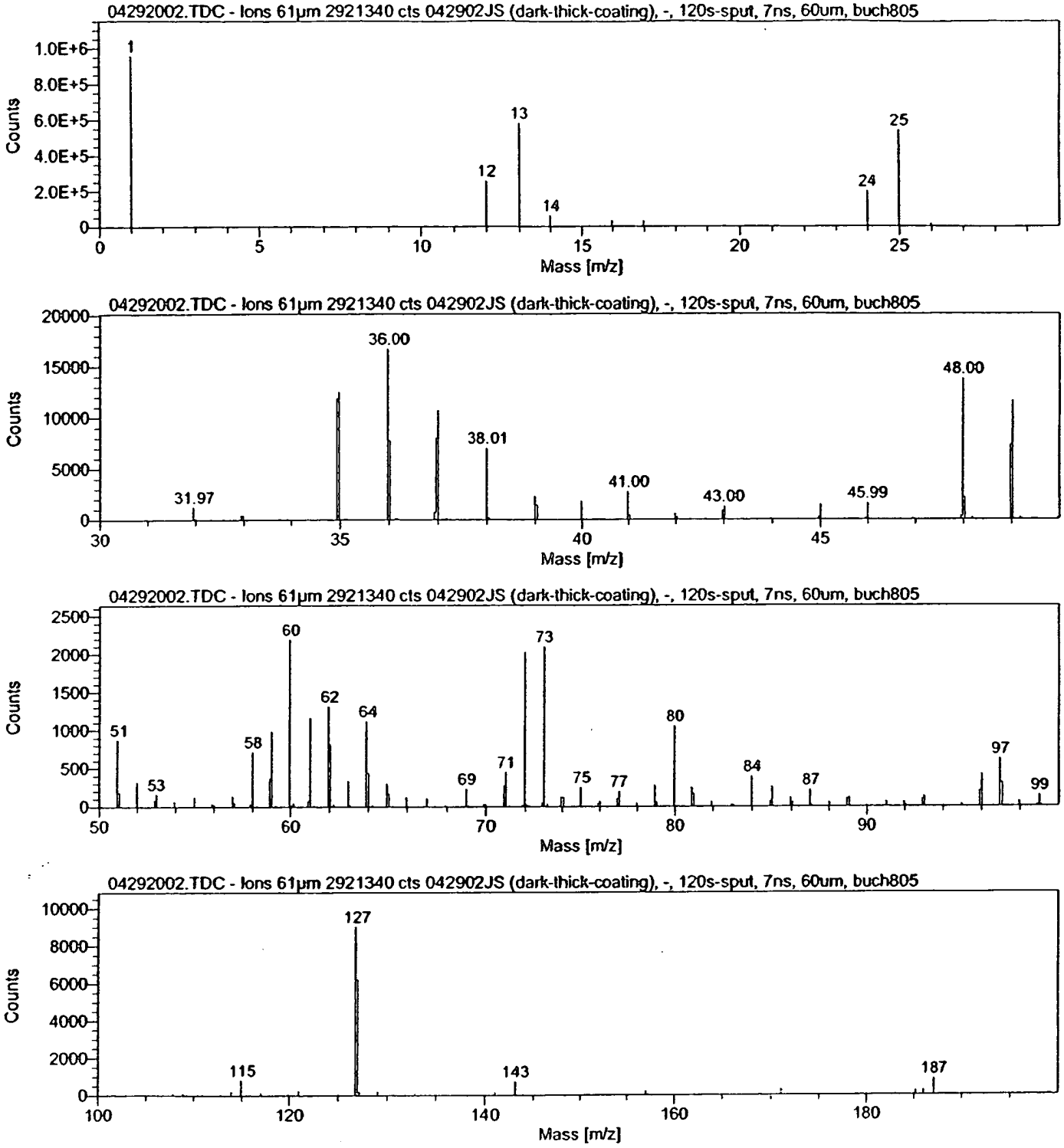
04292002.TDC - Ions 61µm 2921340 cts 042902JS (dark-thick-coating), -, 120s-sput, 7ns, 60um, buch805
Counts
Mass [m/z]
1
12
13
14
24
25
31.97
36.00
38.01
41.00
43.00
45.99
48.00
51
53
58
60
62
64
69
71
73
75
77
80
84
87
97
99
115
127
143
187

Fig. 5

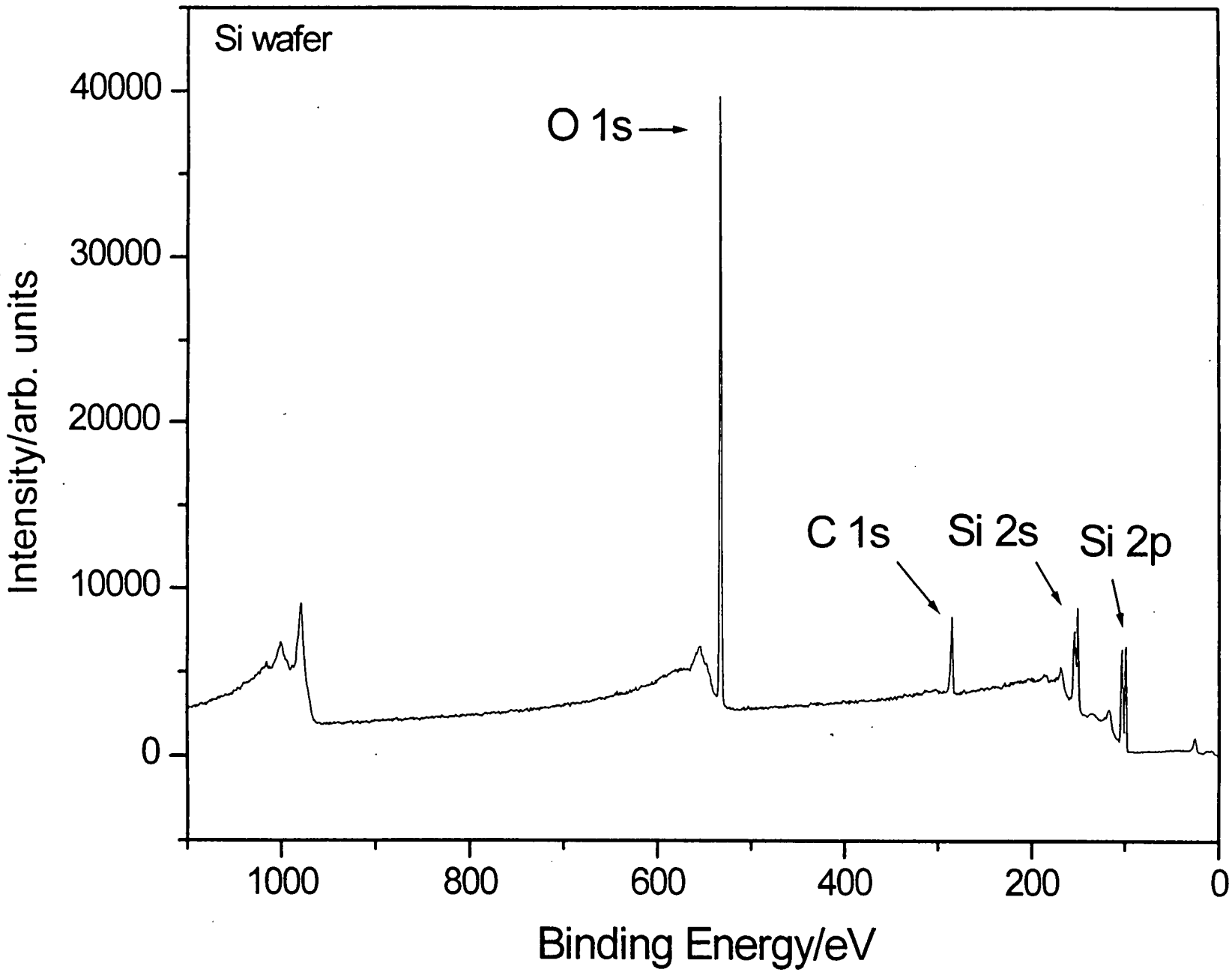
Si wafer
O 1s
C 1s
Si 2s
Si 2p
Intensity/arb. units
40000
30000
20000
10000
0
1000
800
600
400
200
0
Binding Energy/eV

Fig. 6

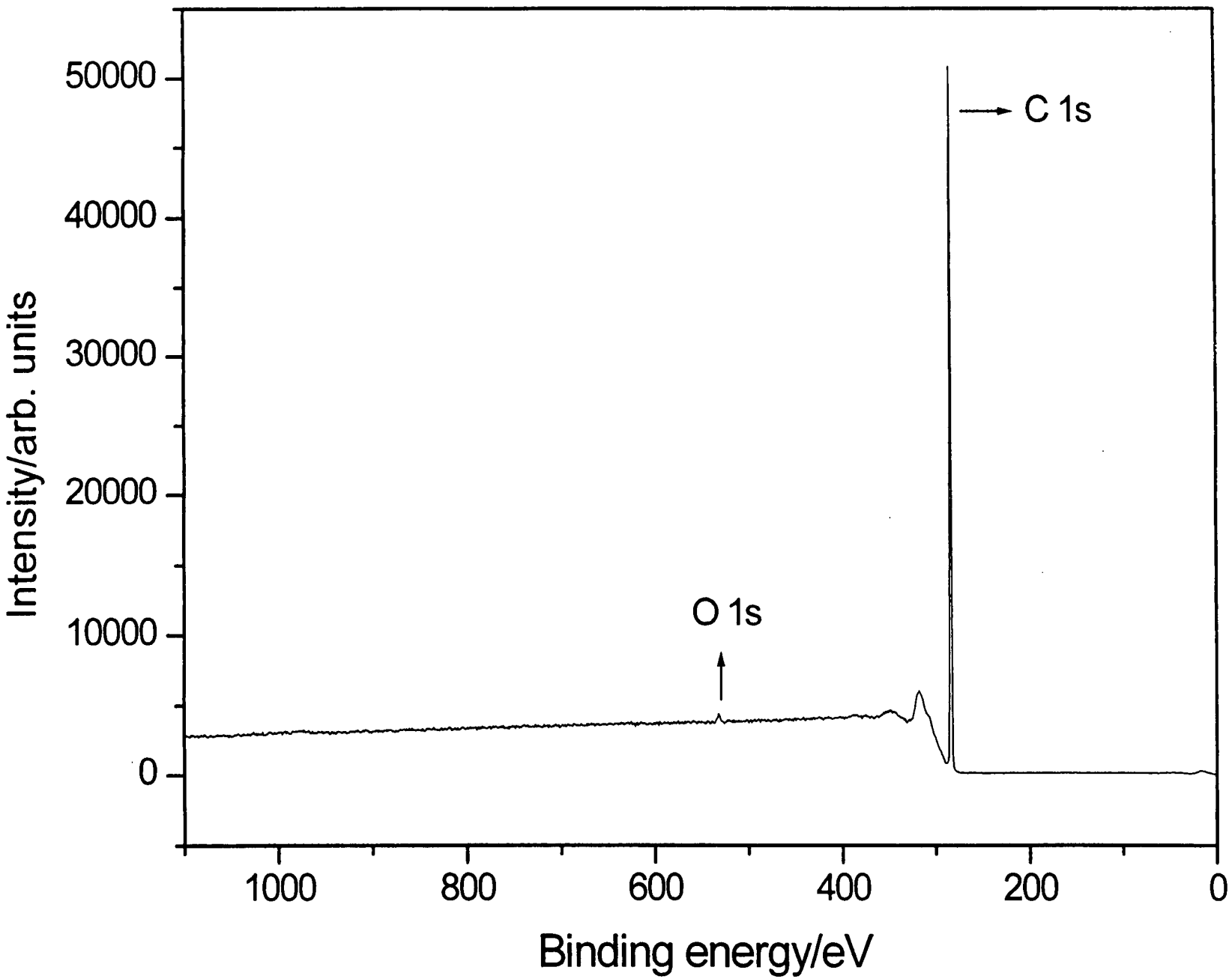
50000
40000
30000
20000
10000
0
Intensity/arb. units
C 1s
O 1s
1000
800
600
400
200
0
Binding energy/eV

Fig. 7

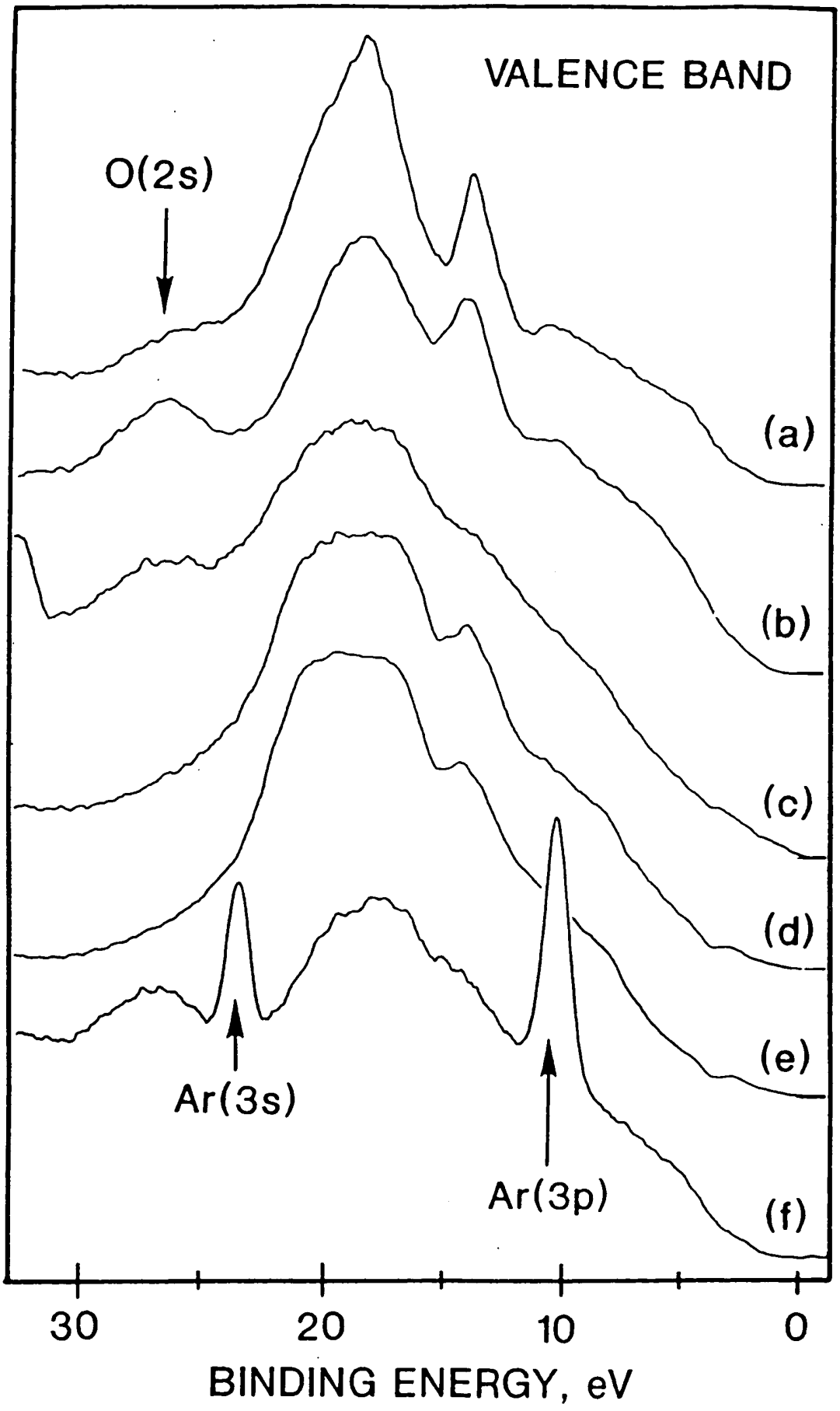
VALENCE BAND
O(2s)
(a)
(b)
(c)
(d)
(e)
(f)
Ar(3s)
Ar(3p)
30
20
10
0
BINDING ENERGY, eV

Fig. 8

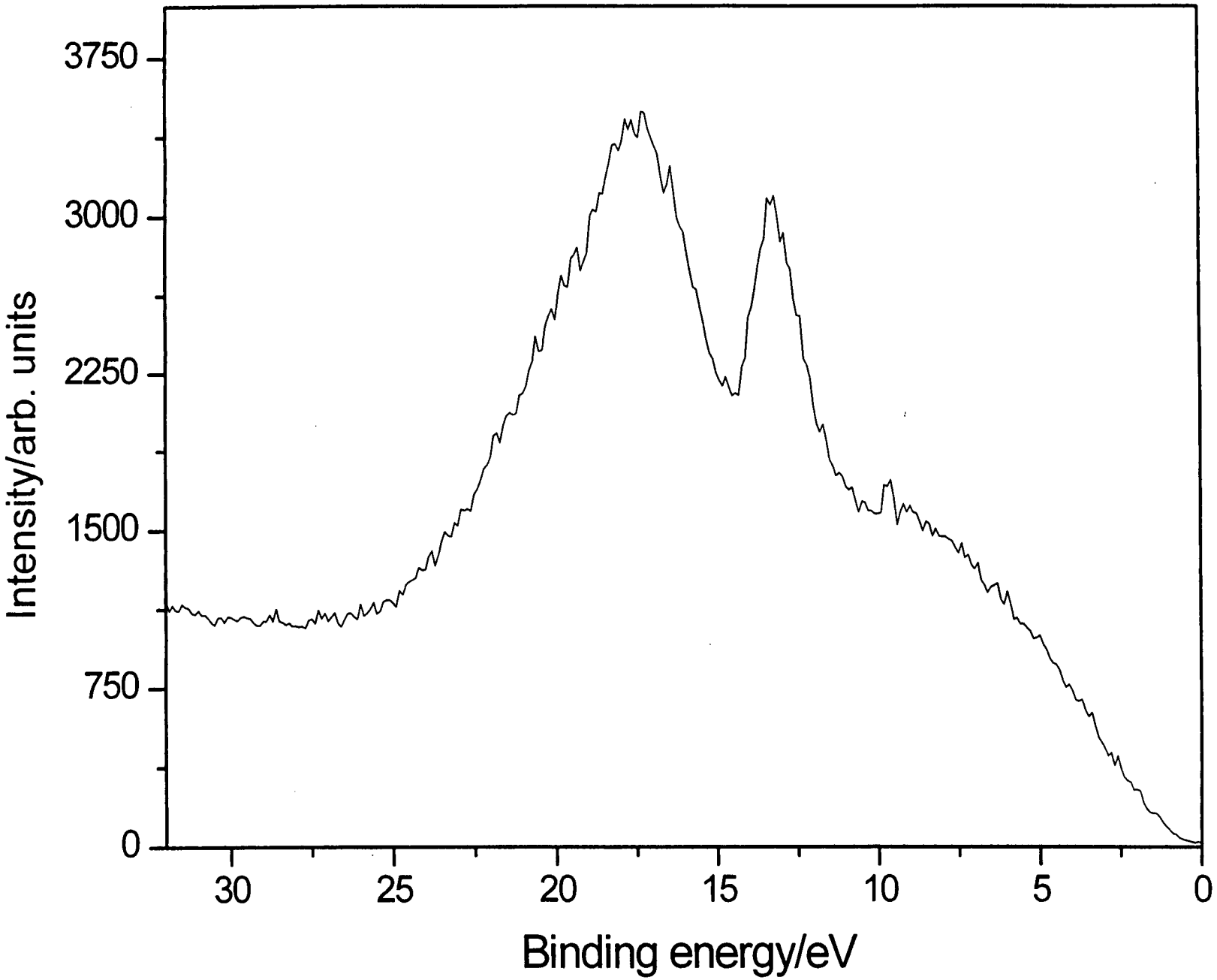
3750
3000
2250
1500
750
0
Intensity/arb. units
30
25
20
15
10
5
0
Binding energy/eV

Fig. 9

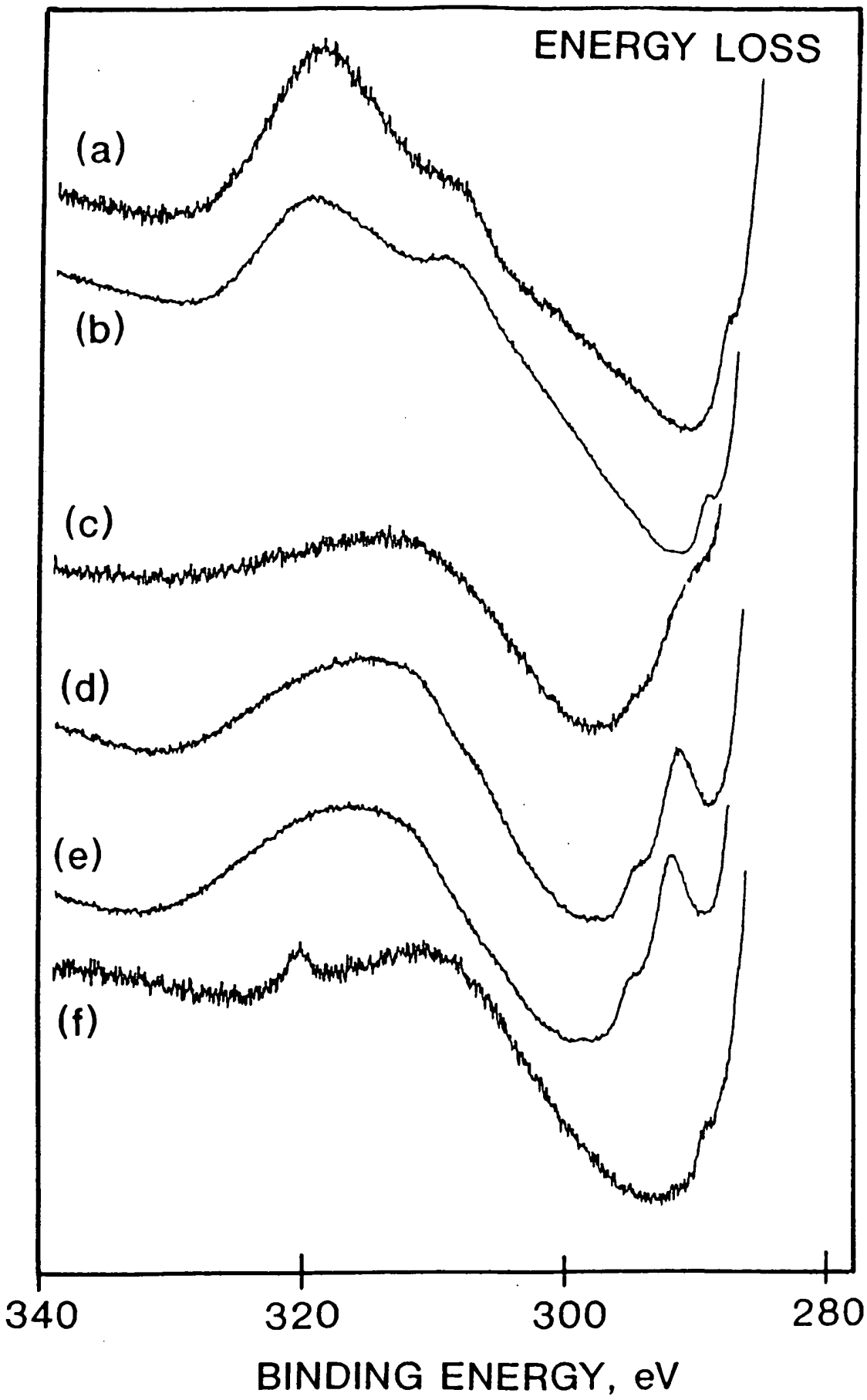

Fig. 10

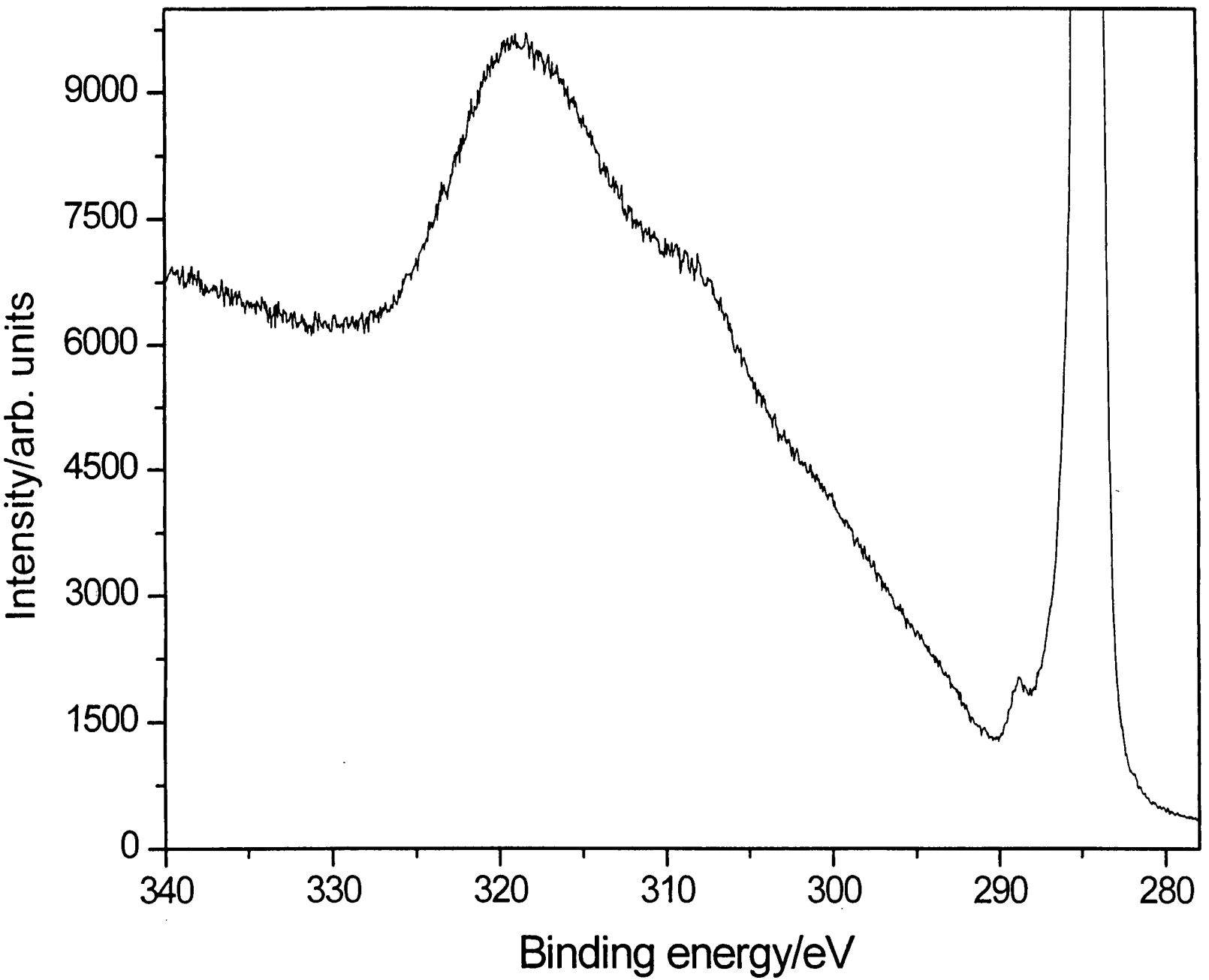
Intensity/arb. units
9000
7500
6000
4500
3000
1500
0
340
330
320
310
300
290
280
Binding energy/eV

Fig. 11

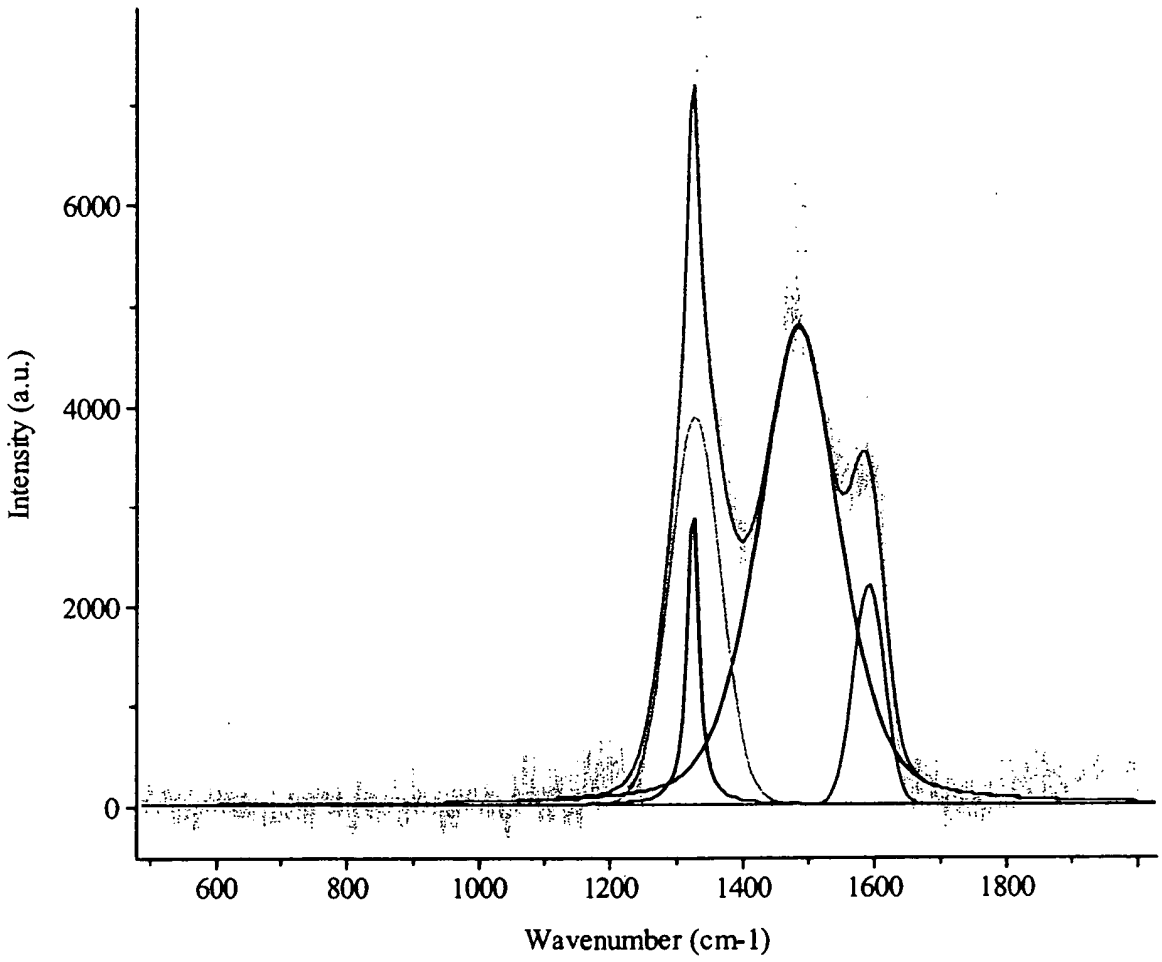
Intensity (a.u.)
6000
4000
2000
0
600
800
1000
1200
1400
1600
1800
Wavenumber (cm-1)

Fig. 12

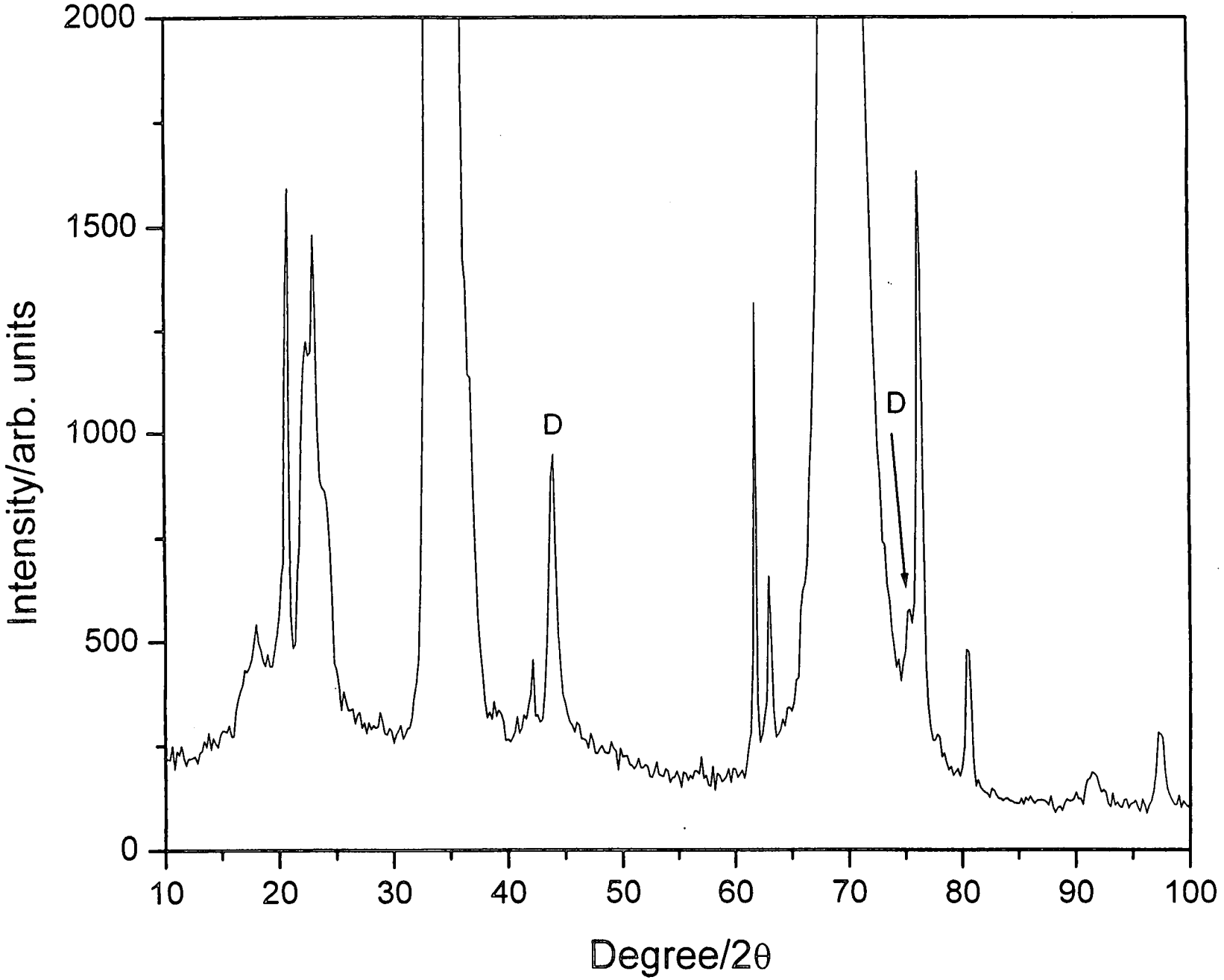
2000
1500
1000
500
0
Intensity/arb. units
D
D
10
20
30
40
50
60
70
80
90
100
Degree/2θ

Fig. 13

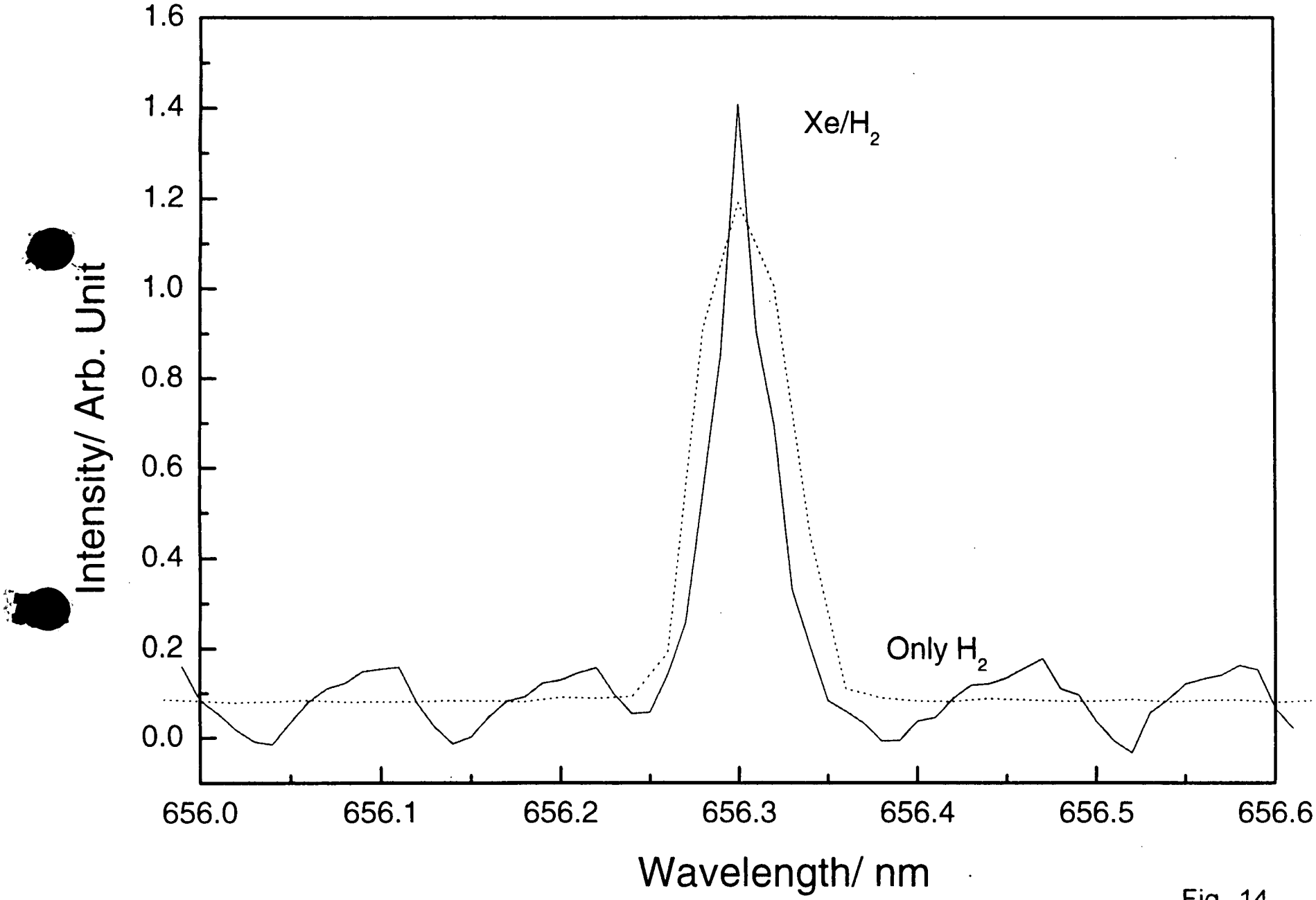
1.6
1.4
1.2
1.0
0.8
0.6
0.4
0.2
0.0
Intensity/ Arb. Unit
Xe/H2
Only H2
656.0
656.1
656.2
656.3
656.4
656.5
656.6
Wavelength/ nm

Fig. 14

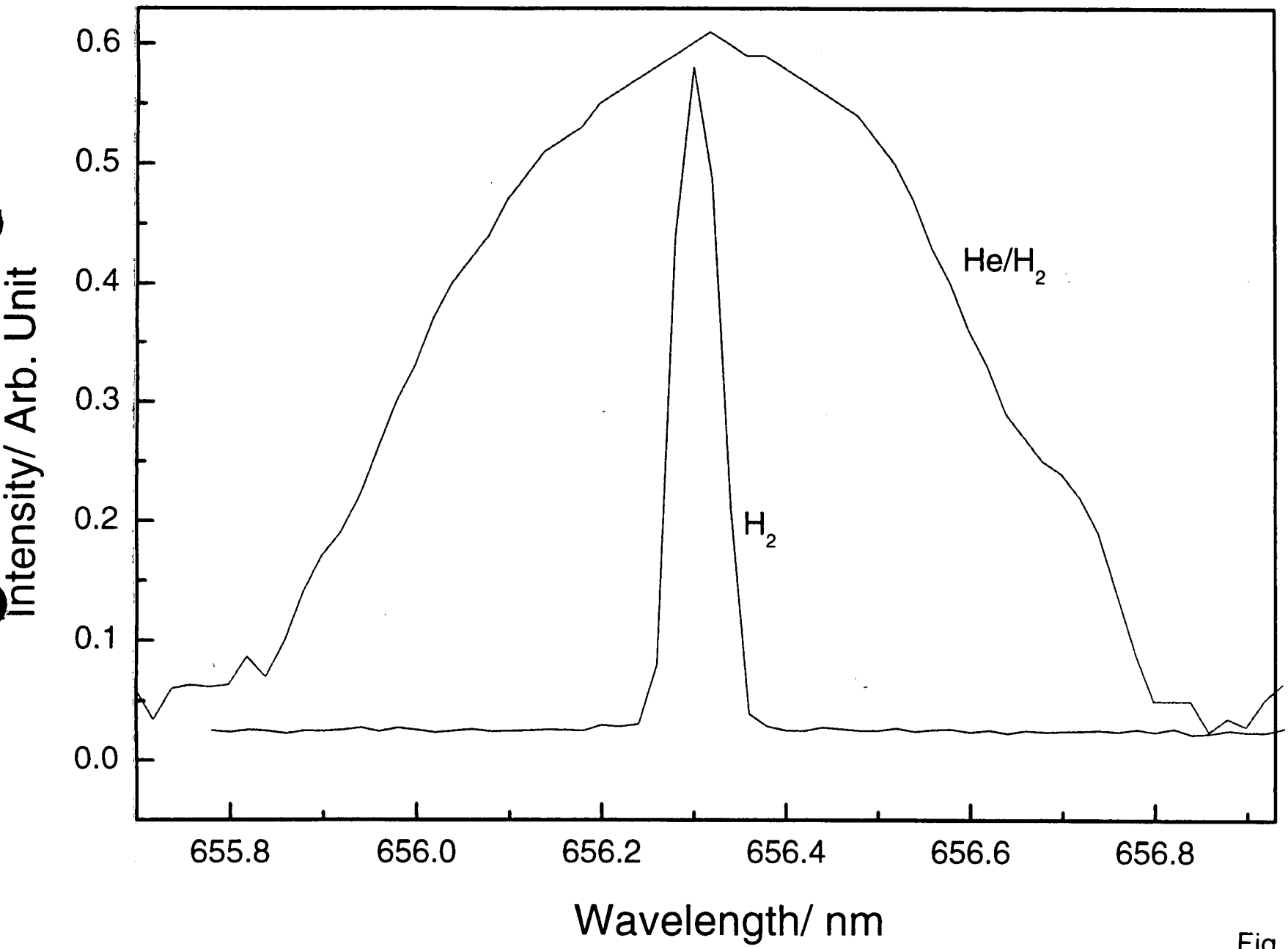
0.6
0.5
0.4
0.3
0.2
0.1
0.0
Intensity/ Arb. Unit
He/H2
H2
655.8
656.0
656.2
656.4
656.6
656.8
Wavelength/ nm

Fig. 15